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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei YAMAZAKI et al.

Art Unit : 2823

Serial No. : 09/773,543

Examiner : Neal Berezny

Filed : February 2, 2001

Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

Commissioner for Patents  
Washington, D.C. 20231

# 13/B  
1-28-03  
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RESPONSE TO ELECTION REQUIREMENT

In response to the action mailed October 18, 2002, please amend the application as noted.

In the claims:

Please amend claims 1, 3, 4, 8, 9, 12, 13, 18, 20, 21, 23, 27, 28, 32, 33 and 37 as follows:

Sub  
C1  
B1

-- 1. (Amended) A semiconductor device comprising:  
a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region, and a channel formation region interposed therebetween;  
a first insulating film formed on said semiconductor layer;  
at least one electrode formed on said first insulating film, and overlapping said channel formation region;  
a source wiring formed on said first insulating film;  
a second insulating film covering at least said at least one electrode and said source wiring; and  
a gate wiring formed on said second insulating film, and connected to said at least one electrode.

3. (Amended) A semiconductor device according to claim 1, wherein said at least one electrode comprises a gate electrode.

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C1